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(54) Title: A METHOD FOR CONVERTING A SENSOR CAPACITANCE UNDER PARASITIC CAPACITANCE CONDITIONS AND A CAPACITANCE-TO-VOLTAGE CONVERTER CIRCUIT

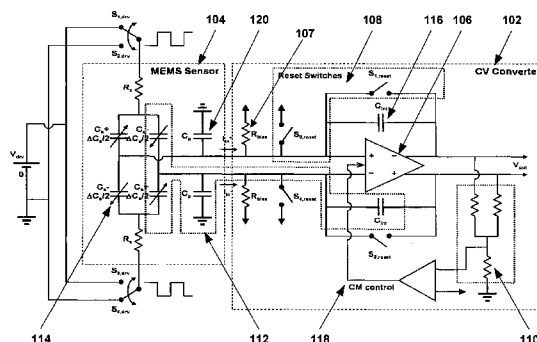


Figure 1

(57) Abstract: A method for converting a sensor capacitance under parasitic capacitance conditions and a capacitance-to-voltage (CV) converter circuit for converting a sensor capacitance under parasitic capacitance conditions are provided. The method comprises the step of using a two stage operational amplifier (op-amp) in non-unity-gain configuration, wherein the two stage op-amp is chosen to be unstable in unity-gain configuration for reducing power consumption.